

**10/726,755****Patent****IBM Docket No. FIS920010385US2**In the claims:

Claims 1-14 (Canceled).

15. (Currently amended) A method of forming a multichip module comprising the steps of:

forming a thin film structure on a temporary carrier;

positioning an electrically insulating frame with respect to a first surface of the thin film structure so that the frame extends beyond a periphery of the thin film structure;

attaching the an electrically insulating frame to the a first surface of the thin film structure;

attaching at least one semiconductor device to the first surface of the thin film structure;

removing the temporary carrier; and

attaching at least one semiconductor device to a second surface of the thin film structure, wherein the first surface is opposed to the second surface and wherein there is interconnectivity through the thin film structure between the semiconductor devices and the frame.

16. (Original) The method of claim 15 wherein the frame comprises an open area through which at least one semiconductor device is exposed.

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17. (Currently amended) The method of claim 15 further comprising the step of applying a stiffening material only between the frame and one of the at least one semiconductor devices.
18. (Previously presented) The method of claim 17 wherein the stiffening material is epoxy.
19. (Currently amended) The method of claim 15 wherein the thin film structure has a thickness of 15 to 250 microns.
20. (Currently amended) The method of claim 15 wherein the electrically insulating frame comprises a ceramic or organic material.
21. (Currently amended) The method of 15 further comprising the step of attaching at least one passive component on one of the opposed surfaces of the thin film structure.